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# Author Correction: ITO-free silicon-integrated perovskite electrochemical cell for light-emission and light-detection

Maria Baeva<sup>1,2,3</sup>, Dmitry Gets<sup>2</sup>, Artem Polushkin<sup>2</sup>, Aleksandr Vorobyov<sup>1</sup>, Aleksandr Goltaev<sup>1</sup>, Vladimir Neplokh<sup>1,4</sup>, Alexey Mozharov<sup>1</sup>, Dmitry V. Krasnikov<sup>5</sup>, Albert G. Nasibulin<sup>5</sup>, Ivan Mukhin<sup>1,4\*</sup> and Sergey Makarov<sup>2,6\*</sup>

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After the publication of this article<sup>1</sup>, it was brought to our attention that calculations of the PeLEC device electroluminescent (EL) efficiency contained a mistake, leading to an inaccurate quantity value. The device's maximum EL efficiency constitutes not '~120 klm/W' but '4.3 lm/W' instead. Correction details are listed below.

1. In the third sentence in the abstract "electroluminescence efficiency of  $1.3 \times 10^5$  lm/W" should be "electroluminescence efficiency of 4.3 lm/W";

2. In the paragraph below Fig. 3, "The maximum EL efficiency of ~120 klm/W is reached at 3.2 V" should be "The maximum EL efficiency of ~4.3 lm/W is reached at

3.2 V";

3. Figure 3.d is replaced exhibiting the accurate data;

4. In the second sentence in the conclusion "which provides light electroluminescence efficiency of  $1.3 \times 10^5$  lm/W" should be "which provides light electroluminescence efficiency 4.3 lm/W".

We would like to apologize for any inconvenience these errors may have caused.

The original article has been updated.

## References

1. Baeva M, Gets D, Polushkin A et al. ITO-free silicon-integrated perovskite electrochemical cell for light-emission and light-detection. *Opto-Electron Adv* 6, 220154 (2023).

## Competing interests

The authors declare no competing financial interests.

<sup>1</sup>Alferov University, Khlopina 8/3, St. Petersburg 194021, Russia; <sup>2</sup>Department of Physics and Engineering, ITMO University, Lomonosova 9, St. Petersburg 197101, Russia; <sup>3</sup>Institute of Automation and Control Processes (IACP), Far Eastern Branch of Russian Academy of Sciences, Ulitsa Radio 5, Vladivostok 690041, Primorsky Krai, Russia; <sup>4</sup>Peter the Great St. Petersburg Polytechnic University, Polytechnicheskaya 29, St. Petersburg 195251, Russia; <sup>5</sup>Skolkovo Institute of Science and Technology, Nobel 3, Moscow 121205, Russia; <sup>6</sup>Qingdao Innovation and Development Center, Harbin Engineering University, Qingdao 266000, China.

\*Correspondence: I Mukhin, E-mail: [imukhin@yandex.ru](mailto:imukhin@yandex.ru); S Makarov, E-mail: [s.makarov@metalab.ifmo.ru](mailto:s.makarov@metalab.ifmo.ru)

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